NSN 5961-01-269-3102

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Unitized Semiconductor Devices - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-269-3102 **Inclosure Material:** Plastic **Overall Length:** Between 0.745 inches and 0.785 inches **Terminal Length:** Between 0.145 inches and 0.200 inches **Overall Height:** Between 0.280 inches and 0.350 inches **Overall Width:** 0.300 inches Joint Electronic Device Engineering Council/jedec/case Outline Designation: Mo-001-ac **Component Name And Quantity:** 5 transistor **Mounting Method: Terminal Semiconductor Material:** Silicon all transistor Voltage Rating In Volts Per Characteristic: -40.0 breakdown voltage, collector-to-base, emitter open all transistor and -40.0 breakdown voltage, collector-to-emitter, base open all transistor and -40.0 breakdown voltage, emitter-to-base, collector open all transistor **Current Rating Per Characteristic:** -40.00 nanoamperes zero-gate-voltage source current preset all transistor and -100.00 nanoamperes zero-gate-voltage source current absolute all transistor **Transfer Ratio:** 40.0 static forward current transfer ratio, common-emitter all transistor and 200.0 static forward current transfer ratio, common-emitter all transistor **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius ambient air **Special Features:** All transistor junction pattern arrangement: pnp **Terminal Type And Quantity:** 14 ribbon Shelf Life: N/a **Unit Of Measure: Demilitarization:** No